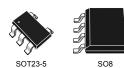
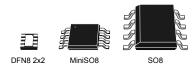


Single, dual, and quad rail-to-rail input/output 8 MHz operational amplifiers

TSV911



TSV912



TSV914





Features

- Rail-to-rail input and output
- Wide bandwidth
- Low power consumption: 820 µA typ.
- Unity gain stability
- High output current: 35 mA
- Operating from 2.5 V to 5.5 V
- Low input bias current, 1 pA typ.
- Low input offset voltage: 1.5 mV max. (A grade)
- ESD internal protection ≥ 5 kV
- Latch-up immunity

Applications

- Battery-powered applications
- Portable devices
- Signal conditioning
- Active filtering
- Medical instrumentation
- Automotive applications

Product status link

TSV911, TSV911A, TSV912, TSV912A, TSV914, TSV914A

Related products

See TSV991, TSV992. TSV994 and TSV991A, TSV992A. TSV994A

for higher speed

Description

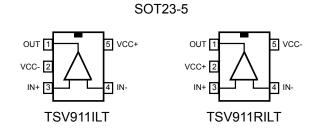
The TSV91x and TSV91xA operational amplifiers (op amps) offer low voltage operation and rail-to-rail input and output, as well as an excellent speed/power consumption ratio, providing an 8 MHz gain-bandwidth product while consuming only 1.1 mA maximum at 5 V. The op amps are unity gain stable and feature an ultra-low input bias current.

The devices are ideal for sensor interfaces, battery-supplied and portable applications, as well as active filtering.

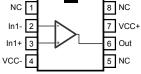


Package pin connections

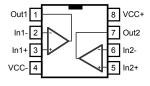
Figure 1. Pin connections for each package (top view)



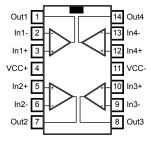




MiniSO8, SO8, DFN8 2x2 (dual)



SO14, TSSOP14



The exposed pad of the DFN8 2x2 package is not internally connected and can be set to V_{CC}^- or left floating.

DS4899 - Rev 12 page 2/28



Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings (AMR)

Symbol	Parameter		Value	Unit	
V _{CC}	Supply voltage (1)		6		
V _{id}	Differential input voltage (2)		±V _{CC}	V	
V _{in}	Input voltage (3)		(V _{CC-}) - 0.2 to (V _{CC+}) + 0.2		
l _{in}	Input current (4)	Input current (4)			
T _{stg}	Storage temperature	Storage temperature			
T _j	Maximum junction temperature		150	°C	
		SOT23-5	250		
		DFN8 2x2	57		
D	The area of a single si	SO8	125		
R _{thja}	Thermal resistance junction to ambient (5) (6)	MiniSO8	190		
		SO14	103		
		TSSOP14	100	°C/W	
		SOT23-5	81		
		SO8	40		
R_{thjc}	Thermal resistance junction to case (5) (6)	MiniSO8	39		
		SO14	31		
		TSSOP14	32		
	HBM: human body model ⁽⁷⁾		5	kV	
	MM: machine model (8)		400		
ESD		SOT23-5, SO8, MiniSO8	1500	V	
	CDM: charged device model (9)	TSSOP14	750		
		SO14			
	Latch-up immunity	200	mA		

- 1. All voltage values, except the differential voltage, are with respect to network ground terminal.
- 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
- 3. V_{CC} V_{IN} must not exceed 6 V
- 4. Input current must be limited by a resistor in series with the inputs
- 5. Short-circuits can cause excessive heating and destructive dissipation.
- 6. R_{th} are typical values
- 7. Human body model: 100 pF discharged through a 1.5 k Ω resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- 8. Machine model: 200 pF charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor $< 5 \Omega$), done for all couples of pin combinations with other pins floating
- Charged device model: all pins plus packages are charged together to the specified voltage and then discharged directly to the ground.

DS4899 - Rev 12 page 3/28



Table 2. Operating conditions

Symbol	Parameter		Value	Unit	
V _{CC}	Supply voltage	-40 °C < T _{op} < 125 °C	2.5 to 5.5		
VGC	0 °C < T _{op} < 125 °C		2.3 to 5.5	V	
V _{icm}	Common mode input voltage range		(V_{CC-}) - 0.1 to (V_{CC+}) + 0.1		
T _{op}	Operating free air temperature range		-40 to 125	°C	

DS4899 - Rev 12 page 4/28



3 Electrical characteristics

Table 3. Electrical characteristics at V_{CC+} = 2.5 V, V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, with R_L connected to $V_{CC}/2$, T = 25 °C (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
C performa	nce						
	05	T _{op} = 25 °C		0.1	4.5		
	Offset voltage, TSV91x	$T_{min} < T_{op} < T_{max}$			7.5		
V_{io}		T _{op} = 25 °C			1.5	mV	
	Offset voltage, TSV91xA	$T_{min} < T_{op} < T_{max}$			3		
$\Delta V_{io}/\Delta T$	Input offset voltage drift			5		μV/°C	
		T _{op} = 25 °C		1	10		
l _{io}	Input offset current (1)	$T_{min} < T_{op} < T_{max}$			100		
	40	T _{op} = 25 °C		1	10	pA	
I _{ib} Inpu	Input bias current (1)	$T_{min} < T_{op} < T_{max}$			100		
	Common mode rejection ratio,20 log	0 V to 2.5 V, V _{out} = 1.25 V, T _{op} = 25 °C	58	75			
CMR	$(\Delta V_{ic}/\Delta V_{io})$	$T_{min} < T_{op} < T_{max}$	53				
		$R_L = 10 \text{ k}\Omega, V_{\text{out}} = 0.5 \text{ V to 2 V}, T_{\text{op}} = 25 \text{ °C}$	80	89		dB	
A_{vd}	Large signal voltage gain	T _{min} < T _{op} < T _{max}	75				
V _{CC} - V _{OH}		R _L = 10 kΩ		15	40		
		$T_{min} < T_{op} < T_{max}$			40		
	High-level output voltage	R _L = 600 Ω		45	150		
		T _{min} < T _{op} < T _{max}			150		
		R _L = 10 kΩ		15	40	m∨	
		$T_{min} < T_{op} < T_{max}$			40	_	
V_{OL}	Low-level output voltage	R _L = 600 Ω		45	150		
		T _{min} < T _{op} < T _{max}			150		
		V _o = 2.5 V, T _{op} = 25 °C	18	32			
	I _{sink}	$T_{min} < T_{op} < T_{max}$	16				
l _{out}		V _o = 0 V, T _{op} = 25 °C	18	35			
	Isource	$T_{min} < T_{op} < T_{max}$	16			– mA	
		No load, V _{out} = V _{CC} /2		0.78	1.1		
I _{CC}	Supply current (per channel)	$T_{min} < T_{op} < T_{max}$			1.1		
C performa	nce			l	ı		
CDD	Cain handwidth product	$R_L = 2 k\Omega$, $C_L = 100 pF$, $f = 100 kHz$,		0			
GBP	Gain bandwidth product	T _{op} = 25 °C		8		MHz	
Fu	Unity gain frequency	$R_L = 2 k\Omega$, $C_L = 100 pF$, $T_{op} = 25 °C$		7.2			
φm	Phase margin	$R_L = 2 k\Omega$, $C_L = 100 pF$, $T_{op} = 25 °C$		45		Degre	

DS4899 - Rev 12 page 5/28



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
G _m	Gain margin	$R_L = 2 k\Omega$, $C_L = 100 pF$, $T_{op} = 25 °C$		8		dB
SR	Slew rate	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}, A_V = 1, T_{op} = 25 \text{ °C}$		4.5		V/µs
e _n	Equivalent input noise voltage	f = 10 kHz, T _{op} = 25 °C		21		nV/√Hz
THD+e _n	Total harmonic distortion	$G = 1$, $f = 1$ kHz, $R_L = 2$ kΩ, BW = 22 kHz, $T_{op} = 25$ °C, $V_{icm} = (V_{CC} + 1)/2$, $V_{out} = 1.1$ V_{pp}		0.001		%

1. Guaranteed by design

DS4899 - Rev 12 page 6/28



Table 4. Electrical characteristics at V_{CC+} = 3.3 V, V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, with R_L connected to $V_{CC}/2$, T = 25 °C (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
		DC performance	'				
	Office truelles as TCV/04v	T _{op} = 25 °C		0.1	4.5		
V	Offset voltage, TSV91x	T _{min} < T _{op} < T _{max}			7.5	m)/	
V_{io}	Officet voltage TSV/04vA	T _{op} = 25 °C			1.5	mV	
	Offset voltage, TSV91xA	$T_{min} < T_{op} < T_{max}$			3		
$\Delta V_{io}/\Delta T$	Input offset voltage drift			5		μV/°C	
ı.	Langua official common (1)	T _{op} = 25 °C		1	10		
l _{io}	Input offset current (1)	$T_{min} < T_{op} < T_{max}$			100		
		T _{op} = 25 °C		1	10	pA	
l _{ib}	Input bias current (1)	$T_{min} < T_{op} < T_{max}$			100		
		0 V to 3.3 V, V _{out} = 1.65 V,		70			
CMR	Common mode rejection ratio, 20 log $(\Delta V_{ic}/\Delta V_{io})$	T _{op} = 25 °C	60	78			
	20.09 (2016.2010)	$T_{min} < T_{op} < T_{max}$	55				
		$R_L = 10 \text{ k}\Omega$, $V_{out} = 0.5 \text{ V to } 2.8 \text{ V}$,	00	00		dB	
A_{vd}	Large signal voltage gain	T _{op} = 25 °C	80	89			
		$T_{min} < T_{op} < T_{max}$	75				
		R _L = 10 kΩ		15	40		
		T _{min} < T _{op} < T _{max}			40		
V _{CC} - V _{OH}		R _L = 600 Ω		45	150		
		T _{min} < T _{op} < T _{max}			150		
		R _L = 10 kΩ		15	40	mV	
.,		T _{min} < T _{op} < T _{max}			40		
V_{OL}	Low-level output voltage	R _L = 600 Ω		45	150	-	
		T _{min} < T _{op} < T _{max}			150		
		V _o = 3.3 V, T _{op} = 25 °C	18	32			
	I _{sink}	T _{min} < T _{op} < T _{max}	16				
l _{out}		V _o = 0 V, T _{op} = 25 °C	18	35			
	I _{source}	$T_{min} < T_{op} < T_{max}$	16			mA	
		No load, V _{out} = V _{CC} /2		0.8	1.1		
I _{CC}	Supply current (per channel)	$T_{min} < T_{op} < T_{max}$			1.1		
C perform	ance	•		l			
		$R_L = 2 \text{ k}\Omega$, $C_L = 100 \text{ pF}$, $f = 100 \text{ kHz}$,					
GBP	Gain bandwidth product	T _{op} = 25 °C		8		MHz	
Fu	Unity gain frequency	R _L = 2 kΩ, C _L = 100 pF, T _{op} = 25 °C		7.2			
φm	Phase margin	R _L = 2 kΩ, C _L = 100 pF, T _{op} = 25 °C		45		Degree	
G _m	Gain margin	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}, T_{op} = 25 \text{ °C}$		8		dB	

DS4899 - Rev 12 page 7/28





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
CD.	Clawrata	$R_L = 2 k\Omega$, $C_L = 100 pF$, $A_V = 1$,		4.5		\//ua
SR Slew rate	T _{op} = 25 °C	4.5			V/µs	
e _n	Equivalent input noise voltage	f = 10 kHz, T _{op} = 25 °C		21		nV/√Hz
		$G = 1, f = 1 \text{ kHz}, R_L = 2 \text{ k}\Omega, BW = 22 \text{ kHz},$				
THD+e _n	Total harmonic distortion	$T_{op} = 25 ^{\circ}\text{C}, V_{icm} = (V_{CC} + 1)/2,$		0.0007		%
		V_{out} = 1.9 V_{pp}				

1. Guaranteed by design

DS4899 - Rev 12 page 8/28



Table 5. Electrical characteristics at V_{CC+} = 5 V, V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, with R_L connected to $V_{CC}/2$, T = 25 °C (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
C performar	nce					
	Office to the real TOVO411	T _{op} = 25 °C		0.1	4.5	
V	Offset voltage, TSV91x	$T_{min} < T_{op} < T_{max}$			7.5	
V_{io}	Office to valte and TOVO4vA	T _{op} = 25 °C			1.5	mV
	Offset voltage, TSV91xA	$T_{min} < T_{op} < T_{max}$			3	
$\Delta V_{io}/\Delta T$	Input offset voltage drift			5		μV/°C
		T _{op} = 25 °C		1	10	
l _{io}	Input offset current (1)	$T_{min} < T_{op} < T_{max}$			100	
		T _{op} = 25 °C		1	10	pA
l _{ib}	Input bias current (1)	$T_{min} < T_{op} < T_{max}$			100	
	Common mode rejection ratio,	0 V to 5 V, V _{out} = 2.5 V, T _{op} = 25 °C	62	82		
CMR	20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	58			
SVR	Supply voltage rejection ratio, 20 log $(\Delta V_{CC}/\Delta V_{io})$	V _{CC} = 2.5 to 5 V	70	86		dB
A_{vd}	Large signal voltage gain	$R_L = 10 \text{ k}\Omega, V_{out} = 0.5 \text{ V to } 4.5 \text{ V},$ $T_{op} = 25 \text{ °C}$	80	91		
		$T_{min} < T_{op} < T_{max}$	75			
		R _L = 10 kΩ		15	40	
., .,		$T_{min} < T_{op} < T_{max}$			40	mV
V _{CC} - V _{OH}	High-level output voltage	R _L = 600 Ω		45	150	
		$T_{min} < T_{op} < T_{max}$			150	
		R _L = 10 kΩ		15	40	
		$T_{min} < T_{op} < T_{max}$			40	
V_{OL}	Low-level output voltage	R _L = 600 Ω		45	150	
		$T_{min} < T_{op} < T_{max}$			150	
		V _o = 5 V, T _{op} = 25 °C	18	32		
	Isink	$T_{min} < T_{op} < T_{max}$	16			
l _{out}		V _o = 0 V, T _{op} = 25 °C	18	35		_
	Isource	$T_{min} < T_{op} < T_{max}$	16			mA
		No load, V _{out} = 2.5 V		0.78	1.1	
I _{CC}	Supply current (per channel)	$T_{min} < T_{op} < T_{max}$			1.1	
C performar	nce			1	1	
GBP	Gain bandwidth product	$R_L = 2 k\Omega$, $C_L = 100 pF$, $f = 100 kHz$, $T_{op} = 25 °C$		8		MHz
Fu	Unity gain frequency	$R_L = 2 k\Omega$, $C_L = 100 pF$, $T_{op} = 25 °C$		7.5		_
φm	Phase margin	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}, T_{op} = 25 \text{ °C}$		45		Degree
G _m	Gain margin	$R_L = 2 k\Omega$, $C_L = 100 pF$, $T_{op} = 25 °C$		8		dB

DS4899 - Rev 12 page 9/28





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
SR	Slew rate	$R_L = 2 k\Omega$, $C_L = 100 pF$, $A_V = 1$, $T_{op} = 25 °C$		4.5		V/µs
0	e _n Equivalent input noise voltage	f = 1 kHz, T _{op} = 25 °C		27		nV/√Hz
c _n		f = 10 kHz, T _{op} = 25 °C		21		IIV/ VIIZ
THD+e _n	Total harmonic distortion	$G = 1$, $f = 1$ kHz, $R_L = 2$ kΩ, $BW = 22$ kHz, $T_{op} = 25$ °C, $V_{icm} = (V_{CC} + 1)/2$, $V_{out} = 3.6$ V_{pp}		0.0004		%

^{1.} Guaranteed by design

DS4899 - Rev 12 page 10/28



4 Electrical characteristic curves

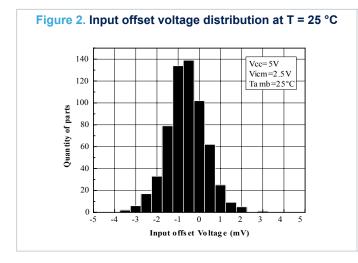


Figure 4. Supply current vs. input common-mode voltage at V_{CC} = 2.5 V

1.0

0.8

1.0

T=25°C

T=40°C

T=40°C

0.0

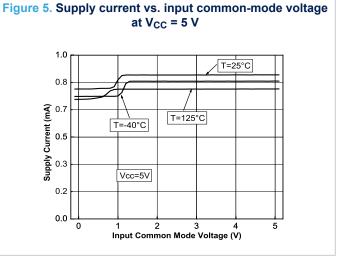
0.0

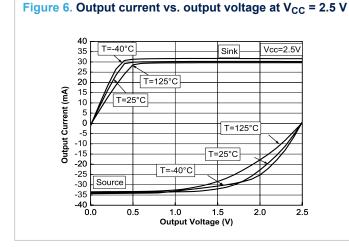
0.0

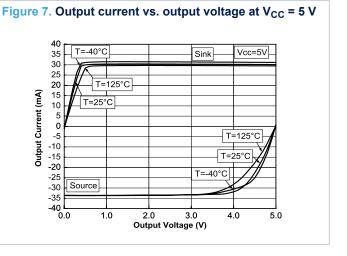
0.0

0.5

Input Common Mode Voltage (V)







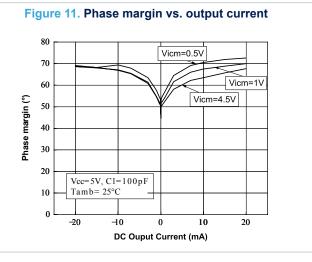
DS4899 - Rev 12 page 11/28

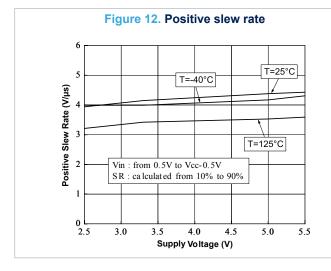


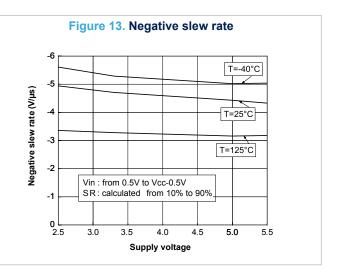
Figure 8. Voltage gain and phase vs. frequency at V_{CC} = 2.5 V and $V_{icm} = 0.5 V$ 40 160 30 120 20 80 Phase 10 40 Gain (dB) -40 -10 -80 Vcc=2.5V, Vicm=0.5V CI=100pF, RI=2kohms, VrI=Vcc/2 -20 -120 -30 Tamb=25°C -160 -40 10⁶ 10 Frequency (Hz)

Figure 9. Voltage gain and phase vs. frequency at V_{CC} = 5.5 V and V_{icm} = 0.5 V 40 160 30 120 20 80 Phase Gain (dB) 10 40 0 -40 -80 -20 Vcc=5.5V, Vicm=0.5V Cl=100pF, Rl=2kOhms, Vrl=Vcc/2 -120 -30 Tamb=25°C -160 -40 10⁶ 10 Frequency (Hz)

Figure 10. Phase margin vs. capacitive load 60 50 Vicm=0.5V Vicm=1V 40 Phase margin (°) Vicm=4.5V 30 20 Vcc=5V, RI=2kOhms Vrl=2.5V 10 Tamb= 25°C 0 L 50 100 150 200 250 300 350 400 450 Capacitive load (pF)







DS4899 - Rev 12 page 12/28

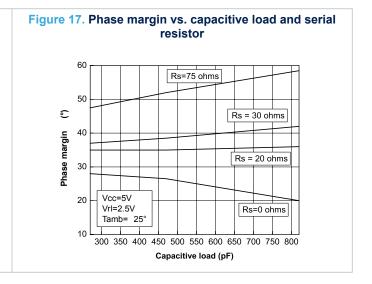


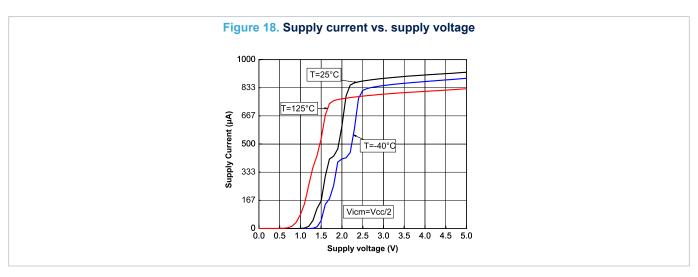
Figure 14. Distortion + noise vs. frequency 0.01 Vcc=3.3V 1E-3 Vout=Vcc-1.4Vpp RI=2kOhms Gain=1 BW=80kHz Vicm=(Vcc+1V)/2 1E-4 10 ППП 100 1000 10000 100000 Frequency (Hz)

Figure 15. Distortion + noise vs. output voltage 1.000 Vcc=3.3V 0.100 Vcc=5V (%) N + QH1 0.010 f=1kHz RI=2kOhms Gain=-3 (13kOhm / 39kOhm) BW=22kHz 0.001 Vicm=Vcc/2 0.000 ____ Output Voltage (Vpp)

Figure 16. Noise vs. frequency

(Vy. = 5V)





DS4899 - Rev 12 page 13/28



5 Application information

5.1 Driving resistive and capacitive loads

These products are low-voltage, low-power operational amplifiers optimized to drive rather large resistive loads above $2 \text{ k}\Omega$.

In a *follower* configuration, these operational amplifiers can drive capacitive loads up to 100 pF with no oscillations. When driving larger capacitive loads, adding a small in-series resistor at the output can improve the stability of the device (figure below shows the recommended in-series resistor values). Once the in-series resistor value has been selected, the stability of the circuit should be tested on bench and simulated with the simulation model.

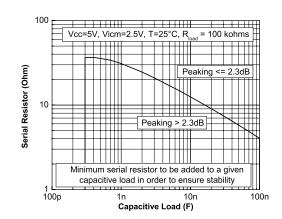


Figure 19. In-series resistor vs. capacitive load

5.2 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.

5.3 Macromodel

An accurate macromodel of the TSV91x is available on STMicroelectronics' web site at: **www.st.com**. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV91x operational amplifiers. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It helps to validate a design approach and to select the right operational amplifier, *but it does not* replace on-board measurements.

DS4899 - Rev 12 page 14/28



6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

6.1 SOT23-5 package information

Figure 20. SOT23-5 package outline

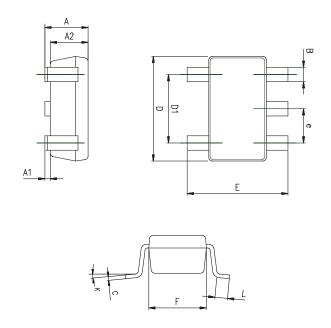


Table 6. SOT23-5 mechanical data

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	0.90	1.20	1.45	0.035	0.047	0.057	
A1			0.15			0.006	
A2	0.90	1.05	1.30	0.035	0.041	0.051	
В	0.35	0.40	0.50	0.014	0.016	0.020	
С	0.09	0.15	0.20	0.004	0.006	0.008	
D	2.80	2.90	3.00	0.110	0.114	0.118	
D1		1.90			0.075		
е		0.95			0.037		
E	2.60	2.80	3.00	0.102	0.110	0.118	
F	1.50	1.60	1.75	0.059	0.063	0.069	
L	0.10	0.35	0.60	0.004	0.014	0.024	
K	0 degrees		10 degrees	0 degrees		10 degrees	

DS4899 - Rev 12 page 15/28



6.2 DFN8 2 x 2 package information

SEATING PLANE

C

PIN#1 ID

PIN#1 ID

BOTTOM VIEW

Figure 21. DFN8 2 x 2 package outline

Table 7. DFN8 2 x 2 mechanical data

	Dimensions							
Ref.	Millimeters			Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	0.51	0.55	0.60	0.020	0.022	0.024		
A1			0.05			0.002		
A3		0.15			0.006			
b	0.18	0.25	0.30	0.007	0.010	0.012		
D	1.85	2.00	2.15	0.073	0.079	0.085		
D2	1.45	1.60	1.70	0.057	0.063	0.067		
E	1.85	2.00	2.15	0.073	0.079	0.085		
E2	0.75	0.90	1.00	0.030	0.035	0.039		
е		0.50			0.020			
L			0.425			0.017		
ddd			0.08			0.003		

DS4899 - Rev 12 page 16/28



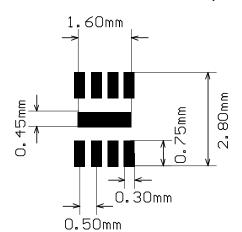


Figure 22. DFN8 2 x 2 recommended footprint

Note: The exposed pad of the DFN8 2x2 package is not internally connected. It can be set to V_{CC}^- or left floating.

DS4899 - Rev 12 page 17/28



6.3 MiniSO8 package information

Figure 23. MiniSO8 package outline

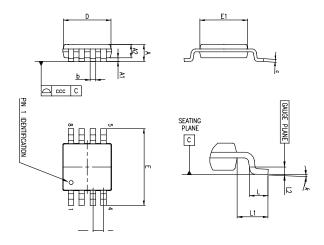


Table 8. MiniSO8 package mechanical data

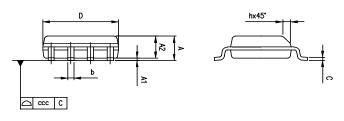
		Dimensions					
Ref.		Millimeters					
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.1			0.043	
A1	0		0.15	0		0.0006	
A2	0.75	0.85	0.95	0.030	0.033	0.037	
b	0.22		0.40	0.009		0.016	
С	0.08		0.23	0.003		0.009	
D	2.80	3.00	3.20	0.11	0.118	0.126	
E	4.65	4.90	5.15	0.183	0.193	0.203	
E1	2.80	3.00	3.10	0.11	0.118	0.122	
е		0.65			0.026		
L	0.40	0.60	0.80	0.016	0.024	0.031	
L1		0.95			0.037		
L2		0.25			0.010		
k	0°		8°	0°		8°	
ccc			0.10			0.004	

DS4899 - Rev 12 page 18/28



6.4 SO8 package information

Figure 24. SO8 package outline



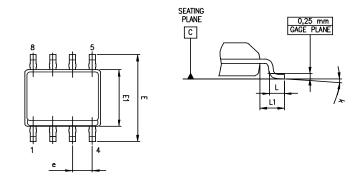


Table 9. SO8 package mechanical data

	Dimensions							
Ref.		Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А			1.75			0.069		
A1	0.10		0.25	0.004		0.010		
A2	1.25			0.049				
b	0.28		0.48	0.011		0.019		
С	0.17		0.23	0.007		0.010		
D	4.80	4.90	5.00	0.189	0.193	0.197		
E	5.80	6.00	6.20	0.228	0.236	0.244		
E1	3.80	3.90	4.00	0.150	0.154	0.157		
е		1.27			0.050			
h	0.25		0.50	0.010		0.020		
L	0.40		1.27	0.016		0.050		
L1		1.04			0.040			
k	0°		8°	0°		8°		
ccc			0.10			0.004		

DS4899 - Rev 12 page 19/28



6.5 TSSOP14 package information

Figure 25. TSSOP14 package outline

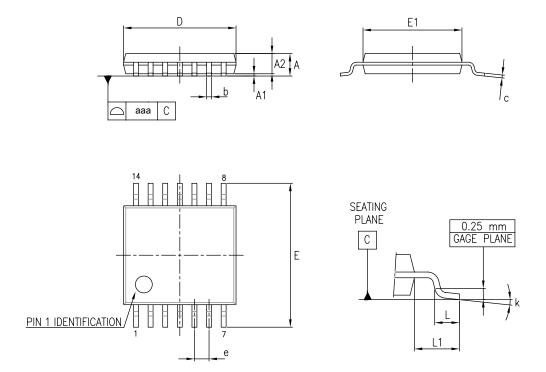


Table 10. TSSOP14 package mechanical data

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.20			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
С	0.09		0.20	0.004		0.0089
D	4.90	5.00	5.10	0.193	0.197	0.201
E	6.20	6.40	6.60	0.244	0.252	0.260
E1	4.30	4.40	4.50	0.169	0.173	0.176
е		0.65			0.0256	
L	0.45	0.60	0.75	0.018	0.024	0.030
L1		1.00			0.039	
k	0°		8°	0°		8°
aaa			0.10			0.004

DS4899 - Rev 12 page 20/28



6.6 SO14 package information

Figure 26. SO14 package outline

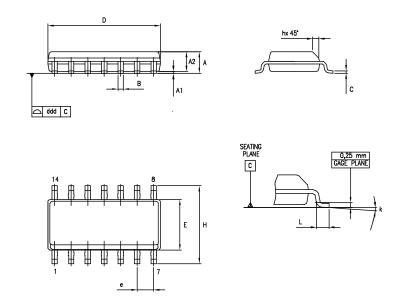


Table 11. SO14 package mechanical data

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
			1.75			0.069
Α	1.35		1.75	0.05		0.068
A1	0.10		0.25	0.004		0.009
A2	1.10		1.65	0.04		0.06
В	0.33		0.51	0.01		0.02
С	0.19		0.25	0.007		0.009
D	8.55		8.75	0.33		0.34
E	3.80		4.0	0.15		0.15
е		1.27			0.05	
Н	5.80		6.20	0.22		0.24
h	0.25		0.50	0.009		0.02
L	0.40		1.27	0.015		0.05
k	8° (max.)					
ddd			0.10			0.004

DS4899 - Rev 12 page 21/28



7 Ordering information

Table 12. Order codes

Order code	Temperature range	Package	Packing	Marking
TSV911IDT		SO8		V911I
TSV911AIDT		506		V911AI
TSV911ILT				K127
TSV911AILT		SOT23-5		K128
TSV911RILT				K125
TSV912IST		MiniSO8		K125
TSV912AIST	-	WillingCo		K126
TSV912IDT		SOS		V912I
TSV912AIDT		SO8		V912AI
TSV912IQ2T		DFN8 2x2		K1Q
TSV914IPT		TSSOP14		V914I
TSV914AIPT		SO14	Tape and reel	V914AI
TSV914IDT				V914I
TSV914AIDT	-40 °C to 125 °C			V914AI
TSV911IYLT (1)		SOT23-5, automotive grade	SOT23-5, automotive grade	K147
TSV911AIYLT (1)		00120-0, automotive grade		K148
TSV911IYDT (1)		SO-8, automotive grade		V911IY
TSV911AIYDT (1)				V911AIY
TSV912IYDT (1)			50-o, automotive grade	V912IY
TSV912AIYDT (1)				V912AIY
TSV912IYST (1)				K147
TSV912AIYST (1)		MiniSO8, automotive grade		K148
TSV914IYDT (1)				V914IY
TSV914AIYDT (1)		SO14, automotive grade		V914AIY
TSV914IYPT (1)				V914IY
TSV914AIYPT (1)		TSSOP14, automotive grade		V914AIY

Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 & Q 002 or equivalent.

DS4899 - Rev 12 page 22/28



Revision history

Table 13. Document revision history

Date	Revision	Changes
28-Aug-2006	1	First release.
		Modified ESD CDM parameter for SO-14 package in Table 2: Absolute maximum ratings.
		Noise parameters updated in Section 2: Electrical characteristics.
07-Jun-2007	2	Added limits in temperature in Section 2: Electrical characteristics.
07-00IP-2007	2	Added automotive grade level description in Table 13: Order codes.
		Added footnote about SO-14 package in Table 13: Order codes.
		Added Figure 16: Phase margin vs. capacitive load and serial resistor.
		Updated footnotes for ESD parameters in Table 2: Absolute maximum ratings.
11-Feb-2008	3	Corrected MiniSO-8 package information in Table 9: MiniSO-8 package mechanical data.
		Added missing markings for order codes TSV911AILT and TSV912AILT in Table 13: Order codes.
		Added input current information in Table 2: Absolute maximum ratings.
		Changed Figure 7 and Figure 8.
00.1.0000	_	Added Chapter 3: Application information.
22-Jun-2009	4	Updated package information in Chapter 4.
		Added automotive order codes: TSV911IYLT, TSV911AIYLT, TSV912IYST, TSV914IYPT and TSV914AIYPT in Table 13: Order codes.
		Added A versions of devices in title on cover page.
17-Sep-2009	5	Modified ESD value for machine model in Table 2: Absolute maximum ratings.
		Added Figure 17: Supply current vs. supply voltage on page 10.
18-Mar-2010	6	Added TSV911RILT in Table 13: Order codes, housed in a SOT23-5 package with a new pinout.
		Added pin connections for TSV911ILT and TSV91RILT on cover page.
		Added Table 1: Device summary on cover page.
	7	Modified supply voltage value in Table 3.
24-Jun-2010		Corrected typical value of DV _{io} in Table 4, Table 5 and Table 6.
		Added TSV911RILT, TSV911IYDT and TSV911AIYDT order codes in Table 13.
		Modified Note 2 under Table 13.

DS4899 - Rev 12 page 23/28



Date	Revision	Changes
06-Mar-2012	8	Added DFN8 2x2 package and ordering information for TSV912 device to Chapter 4 and Chapter 5.
		Updated layout
		Section 2: replaced DV _{io} /DT by Δ V _{io} / Δ T.
27-Nov-2015	9	Section 5.2: updated name of package and title of drawings and table; added note about exposed pad.
		Table 13: "Order codes": removed obsolete order codes (TSV911ID, TSV911AID, TSV912ID, TSV912ID, TSV914ID, TSV914AID).
		Added silhouettes of packages to cover page
	10	Placed pinout diagrams in Section 2: "Package pin connections"
		Added Related products
29-Aug-2016		Description: added footnote 1
C		Section 7.2: "DFN8 2 x 2 package information": modified note about the exposed pad.
		Section 8: "Ordering information": removed note regarding "moisture
		sensitivity level 1"
10-Oct-2019	11	Updated Table 12. Order codes.
20-Nov-2019	12	Updated cover page.

DS4899 - Rev 12 page 24/28



Contents

1	Pac	kage pin connections	2
2	Abs	olute maximum ratings and operating conditions	3
3	Elec	ctrical characteristics	5
4	Elec	ctrical characteristic curves	
5	Арр	olication information	14
	5.1	Driving resistive and capacitive loads	14
	5.2	PCB layouts	14
	5.3	Macromodel	14
6	Pac	kage information	
	6.1	SOT23-5 package information	15
	6.2	DFN8 2 x 2 package information	15
	6.3	MiniSO8 package information	18
	6.4	SO8 package information	19
	6.5	TSSOP14 package information	20
	6.6	SO14 package information	21
7	Ord	ering information	
Rev	ision	history	23



List of tables

Table 1.	Absolute maximum ratings (AMR)	. 3
Table 2.	Operating conditions	. 4
Table 3.	Electrical characteristics at $V_{CC+} = 2.5 \text{ V}$, $V_{CC-} = 0 \text{ V}$, $V_{icm} = V_{CC}/2$, with R_L connected to $V_{CC}/2$, $T = 25 ^{\circ}C$ (unless	;
	otherwise specified)	. 5
Table 4.	Electrical characteristics at $V_{CC+} = 3.3 \text{ V}$, $V_{CC-} = 0 \text{ V}$, $V_{icm} = V_{CC}/2$, with R_L connected to $V_{CC}/2$, $T = 25 ^{\circ}C$ (unless	;
	otherwise specified)	. 7
Table 5.	Electrical characteristics at $V_{CC+} = 5 \text{ V}$, $V_{CC-} = 0 \text{ V}$, $V_{icm} = V_{CC}/2$, with R_L connected to $V_{CC}/2$, $T = 25 ^{\circ}C$ (unless	
	otherwise specified)	. 9
Table 6.	SOT23-5 mechanical data	15
Table 7.	DFN8 2 x 2 mechanical data	16
Table 8.	MiniSO8 package mechanical data	18
Table 9.	SO8 package mechanical data	19
Table 10.	TSSOP14 package mechanical data	20
Table 11.	SO14 package mechanical data	21
Table 12.	Order codes	22
Table 13.	Document revision history	23

DS4899 - Rev 12 page 26/28



List of figures

Figure 1.	Pin connections for each package (top view)	. 2
Figure 2.	Input offset voltage distribution at T = 25 °C	11
Figure 3.	Input offset voltage distribution at T = 125 °C	11
Figure 4.	Supply current vs. input common-mode voltage at V _{CC} = 2.5 V	11
Figure 5.	Supply current vs. input common-mode voltage at V _{CC} = 5 V	11
Figure 6.	Output current vs. output voltage at V _{CC} = 2.5 V	11
Figure 7.	Output current vs. output voltage at V _{CC} = 5 V	
Figure 8.	Voltage gain and phase vs. frequency at V_{CC} = 2.5 V and V_{icm} = 0.5 V	12
Figure 9.	Voltage gain and phase vs. frequency at V_{CC} = 5.5 V and V_{icm} = 0.5 V	12
Figure 10.	Phase margin vs. capacitive load	12
Figure 11.	Phase margin vs. output current	12
Figure 12.	Positive slew rate	12
Figure 13.	Negative slew rate	12
Figure 14.	Distortion + noise vs. frequency	13
Figure 15.	Distortion + noise vs. output voltage	13
Figure 16.	Noise vs. frequency	13
Figure 17.	Phase margin vs. capacitive load and serial resistor	13
Figure 18.	Supply current vs. supply voltage	13
Figure 19.	In-series resistor vs. capacitive load	14
Figure 20.	SOT23-5 package outline	15
Figure 21.	DFN8 2 x 2 package outline	16
Figure 22.	DFN8 2 x 2 recommended footprint	17
Figure 23.	MiniSO8 package outline	18
Figure 24.	SO8 package outline	19
Figure 25.	TSSOP14 package outline	20
Figure 26.	SO14 package outline	21

DS4899 - Rev 12 page 27/28



IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2019 STMicroelectronics - All rights reserved

DS4899 - Rev 12 page 28/28